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Honghong Wang, Tae Beom Park, Soohyeon Shin, Harim Jang, Eric D. Bauer, and Tuson Park

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Field-induced multiple quantum phase transitions in the antiferromagnetic Kondo lattice compound CeRhAl₄Si₂

Honghong Wang^{1#}, Tae Beom Park^{1,2#}, Soohyeon Shin^{1,3}, Harim Jang¹, Eric D. Bauer⁴, Tuson Park^{1*}

¹Center for Quantum Materials and Superconductivity (CQMS) and Department of Physics, Sungkyunkwan University, Suwon 16419, South Korea ²Institute of basic science, Sungkyunkwan University, Suwon 16419, South Korea ³Laboratory for Multiscale Materials Experiments, Paul Scherrer Institut, CH-5232 Villigen PSI, Switzerland

⁴Los Alamos National Laboratory - Los Alamos, NM 87545, USA

We report a comprehensive phase diagram of the antiferromagnetic Kondo lattice compound CeRhAl $_4$ Si $_2$ down to 0.3 K by investigating electrical resistivity, magnetoresistivity, and Hall resistivity under the magnetic field along the c-axis. At zero field, CeRhAl $_4$ Si $_2$ undergoes two successive antiferromagnetic transitions at $T_{\rm N1}$ = 14.2 K and $T_{\rm N2}$ = 8.4 K, respectively. Upon applying magnetic field, the first-order transition of $T_{\rm N2}$ is continuously suppressed at the critical field of 5.5 T. On the other hand, the smooth suppression of the second-order transition of $T_{\rm N1}$ terminates at a tricritical point of 6.6 T and 4.7 K followed by a first-order transition line and an additional new phase transition line, which are monotonically suppressed at 6.7 T and 7.2 T, respectively, implying the field-induced multiple quantum phase transitions. Particularly, in the paramagnetic region before the Fermi liquid behavior is fully developed, a quantum critical phase with non-Fermi liquid behavior is revealed, indicating a potential spin liquid state that was predicted from the global quantum phase diagram. These results suggest that CeRhAl $_4$ Si $_2$ is a promising candidate to study a quantum phase transition that occurs in electronic systems with high degree of frustration.

The physics of quantum criticality has been one of the foremost challenges in strongly correlated electron systems, which is regarded as a key to understanding the important issues including the nature of unconventional superconductivity and non-Fermi liquid (nFL) behavior

[1,2]. In contrast to the classical phase transition driven by thermal fluctuations, the quantum phase transition (QPT) is triggered by quantum fluctuations at zero temperature via non-thermal parameters such as pressure, chemical substitution, or magnetic field [3]. Heavy-fermion (HF) compounds are prototype systems to study the QPT owing to the delicate competition between the Kondo effect and the Ruderman-Kittel-Kasuya-Yosida interaction that promote a non-magnetic and magnetic ground state, respectively. Various types of quantum criticality, including the Kondo breakdown type [4] and the spin-density-wave type [5], have been revealed in HF systems [6-8]. Therefore, it is instructive to broaden the materials basis to establish a universal understanding of the rich variety of quantum critical points (QCPs).

 $CeT_mAl_{2m+2}Si_2$ (T = Rh, Ir, Pt) is a family of HF systems, which crystallize in a tetragonal structure (space group P4/mmm) and is composed of two alternate stacking of a Ce-containing BaAl₄-type layer and a T-containing AuAl₂-type block along the c-axis [9,10]. The systematically tunable dimensionality has attracted attention to this family, which could provide the key to controlling the nature of QCP [11,12] and the superconducting transition temperature [13]. However, the quantum criticality in this $CeT_mAl_{2m+2}Si_2$ series has yet to be fully unveiled due to the insufficient study at low temperatures.

CeRhAl₄Si₂, which belongs to the class with m = 1, is an antiferromagnetic (AFM) HF compound that undergoes two successive AFM transitions of $T_{N1} = 14.2$ K and $T_{N2} = 8.4$ K at 0 T [9,10], where T_{N2} is the magnetic transition from an incommensurate with $\mathbf{k}_{IC} = (0.016, 0.016, 1/2)$ to a commensurate structure with $\mathbf{k}_{C} = (0, 0, 1/2)$ [14-16]. When subjected to a magnetic field, these two AFM transitions are suppressed [10], implying a potential field-induced QCP in this compound. To investigate the quantum criticality, we carried out the measurements at low temperatures, particularly at temperatures below 1.8 K, which have not been performed in the previous report [10]. Here, we present in-plane low-temperature transport measurements down to 0.3 K on CeRhAl₄Si₂ with the applied field along the c-axis. Our results demonstrate that, under field, the lower AFM transition T_{N2} retains first-order character, while the higher AFM transition T_{N1} changes its nature from second to first order accompanied by the appearance of a new phase. With further increasing field, the first-order transition and the new phase are suppressed at 6.7 T

and 7.2 T, respectively, indicating field-induced multiple quantum phase transitions. Furthermore, an evidence for the nFL behavior is observed in the intermediate phase between the ordered phase and the Fermi liquid (FL) region, suggesting a possible field-induced spin liquid state [17].

Single crystals of CeRhAl₄Si₂ were synthesized using the Al/Si flux method as described earlier [9]. All the measurements were performed using the standard six-probe alternating current technique on a rectangular platelet with dimensions of 0.94 x 0.32 x 0.05 mm³, with the current flowing within the *ab*-plane and the applied magnetic field parallel to the *c*-axis. The low-resistance contacts were obtained by spot welding 25 µm diameter Pt wires onto the sample. Magnetoresistivity and Hall resistivity were measured simultaneously by conducting isothermal field sweeps and accurately determined by reversing the magnetic field. The specific heat was carried out using a homemade calorimetry setup employing a thermal relaxation method. A ³He refrigerator was used to control temperature down to 0.3 K and magnetic field up to 9 T.

Figure 1 shows the temperature dependence of the in-plane resistivity $\rho_{xx}(T)$ for CeRhAl₄Si₂ under various magnetic fields applied along the c-axis $(B \parallel c)$. At zero field, two AFM transitions are detected in the low-temperature measurements, which is consistent with the previous reports [9,10]. The lower AFM transition at $T_{\rm N2} = 8.4$ K appears as an abrupt jump in the resistivity and a sharp peak in the specific heat. On the other hand, for the higher AFM transition at $T_{\rm N1} = 14.2$ K, there is a relatively weak slope change in the resistivity, which can be discernible from the first derivative of resistivity (not shown) and the clear cusp feature in the specific heat as shown in the inset of Fig. 1(a). The hysteresis behavior of the resistivity and the shape of the sharp peak in the specific heat support that the transition at $T_{\rm N2}$ is of a first-order nature. With applying field, $T_{\rm N2}$ shifts toward lower temperatures and is completely suppressed below 0.3 K at 5.7 T (Fig. 1(a)). The hysteresis behavior becomes clearer under field, indicating that $T_{\rm N2}$ retains the nature of a first-order transition. Accompanied by the suppression of $T_{\rm N1}$, the signature corresponding to $T_{\rm N1}$ becomes more visible with increasing field, which shows as a clear kink and then becomes an upturn in $\rho_{xx}(T)$ (Fig. 1(a-b)). As the field further increases to 6.6 T, hysteresis appears near the upturn, which exceeds the experimental error and is enhanced with an increase in the field, indicating that the character of $T_{\rm N1}$ changes from second to first order. This first-order transition is

further suppressed by increasing magnetic field and becomes unresolvable above 7.0 T (Fig. 1(c)). With further increasing field, a T^2 dependence is observed at fields higher than 7.5 T, as shown in Fig. 1(d), implying the recovery of FL behavior.

To confirm the evolution of the two AFM transitions with the field observed in $\rho_{xx}(T)$, the field-dependent magnetoresistivity $\rho_{xx}(B)$ was performed in the transverse geometry with the field applied parallel to the c-axis and the current within the ab-plane at selected temperatures. The isothermal $\rho_{xx}(B)$ at 0.3 K with increasing (solid symbols) and decreasing (open symbols) field sweeps is presented in Fig. 2(a). Analogous to the profiles observed in CeAuSb₂ [18], YbAgGe [19], CePdAl [20], and CePtIn₄ [21], $\rho_{xx}(B)$ initially increases with field (which is a typical characteristic of AFM order), jumps sharply through the first metamagnetic transition (MMT) at B_1 , is almost flat, and then decreases sharply across the second MMT at B_2 . It is noteworthy that $\rho_{xx}(B)$ shows a clear hysteresis at two MMTs in the field return cycle. The first-order nature of these transitions is consistent with the hysteresis observed in the $\rho_{xx}(T)$ measurements. At higher fields, a shoulder appearing at B_3 is indicative of a new field-induced phase transition. With further increasing field, a local minimum of $\rho_{xx}(B)$ occurs at B_4 , which can be ascribed to the competition between the positive contribution from the cyclotron motion of the conduction electrons and the negative contribution from the suppression of spin fluctuations by the applied field [10,21]. Above B_4 , the contribution associated with the cyclotron motion of electrons dominates and the positive slope is observed as in the normal metals. The sequence of the multiple transitions can be unambiguously deduced from the first derivative of $\rho_{xx}(B)$, as shown in Fig. 2(b).

Figure 2(c) displays the isothermal Hall resistivity $\rho_{xy}(B)$ at 0.3 K, which was carried out simultaneously with $\rho_{xx}(B)$ to explore the possible changes in the electronic structure across the critical fields. Similar to the features in the $\rho_{xx}(B)$, each transition can be identified in $\rho_{xy}(B)$ as well. The sudden changes in $\rho_{xy}(B)$ appear when the field crosses the two MMTs at B_1 and B_2 , which can be related to the reconstruction of the Fermi surface [22-24]. As the field is further increased, a clear kink is observed at B_3 . For field higher than B_4 , $\rho_{xy}(B)$ shows a linear field dependence (red line), suggesting the formation of the FL state, which is coincident with the

recovery of the positive slope in $\rho_{xx}(B)$. Similar field dependence is also observed in YbAgGe at the critical field above which FL state is formed [25]. Figures 2(d-f) show representative field-dependent $\rho_{xx}(B)$, $d\rho_{xx}(B)/dB$, and $\rho_{xy}(B)$, respectively, at various temperatures below 6 K. As the temperature increases, the changes at the two MMTs remain sharp and shift to lower fields, while the feature for the third phase gradually weakens and cannot be discerned at temperatures above 2 K.

In accordance with $\rho_{xx}(B)$ and $\rho_{xy}(B)$, the phase boundaries can be established by the specific heat (C) measurements. Figure 3 shows the field dependence of specific heat at 0.3 K, plotted as C(B)/T. It clearly reveals a sudden jump across B_1 and reaches a pronounced maximum at B_2 , corresponding to the two metamagnetic transitions. Moreover, the appearance of a broad kink at B_3 is consistent with the formation of a new field-induced phase. The enhancement of C/T is suggestive of the magnetic fluctuations associated with the underlying QCP.

The results obtained from the above experimental measurements are summarized in the temperature-field (T-B) phase diagram in Fig. 4 (see also Supplementary Material). The lower AFM phase, marked as AFM2, is fully suppressed at the critical field $B_{c1} = 5.5$ T and its first-order nature is clearly evidenced by the large hysteresis behavior in $\rho_{xx}(T)$, $\rho_{xx}(B)$, and $\rho_{xy}(B)$. However, the smooth suppression of the higher AFM phase, denoted as AFM1, is terminated by the change from a second- to first-order transition at about 6.6 T and 4.7 K, which is manifested by the appearance of the moderate hysteresis in $\rho_{xx}(T)$, $\rho_{xx}(B)$, and $\rho_{xy}(B)$. This first-order transition is suppressed at the critical field $B_{c2} = 6.7$ T. The vertical phase boundary line at B_{c2} indicates that the field-induced QCP observed in YbRh₂Si₂ [26] is avoided. In addition, a new phase, represented by M, starts to appear at the critical field $B_{c3} = 7.2$ T and increases with a decrease in the field. The appearance of M phase is reminiscent of the d-phase in YbAgGe [27,28]. Considering the similarities between the phase diagram in these two compounds, it can be conjectured that there is a putative tricritical point at about 6.6 T and 4.7 K where the M phase emerges and the AFM1 phase becomes a first-order transition. The M phase of CeRhAl₄Si₂ in magnetic field may correspond to a new magnetic state with a different ordering wavevector. Further measurements of the magnetic structure with $B \parallel c$ are necessary to clarify the nature of the M phase.

In addition to the complexity of field-induced multiple quantum phase transitions, the characteristic of the paramagnetic (PM) phase is also intriguing. The power law analysis of $\rho_{xx}(T)$, $\rho_{xx}(T) = \rho_0 + AT^n$, was carried out above 7 T. As shown in the inset of Fig. 4, n is initially smaller than 2 in the PM phase and gradually increases to 2 at $B_{c4} = 7.7$ T, signaling that the FL state is recovered in the high-field regime. The critical field B_{c4} is in agreement with the recovery of the positive slope in $\rho_{xx}(B)$ and the linear-field dependence of $\rho_{xy}(B)$ (Fig. 2). These discoveries indicate that, preceding the development of the FL state, there is an intermediate phase ($B_{c3} < B <$ B_{c4}) within which $\rho_{xx}(T)$ exhibits nFL behavior. We note that similar quantum critical phase has been reported in other HF systems, such as YbAgGe [19,28], CePdAl [29,30], Ir substituted YbRh₂Si₂ [31], and Ge substituted YbRh₂Si₂ [32]. The global phase diagram for HF metals [17], which is spanned by two parameters of the Kondo coupling (J_K) and the magnetic frustration or the spatial dimensionality (G), provides a possible explanation for the quantum critical phase. With the application of field, the CeRhAl₄Si₂ system may follow a trajectory that goes through a spin liquid state when it evolves from the magnetic ordered phase to the PM phase. More measurements at even lower temperatures, especially that are sensitive to the low-energy spin excitations, would be desirable to understand the quantum spin liquid state. In addition, in the $CeT_mAl_{2m+2}Si_2$ family, the thickness of the TAl_2 block can be enlarged by increasing m, thus, resulting in the increase of the distance between the adjacent Ce planes. The decrease of the effective dimensionality, consequently, is expected to increase the degree of frustration G, placing $CeT_mAl_{2m+2}Si_2$ with larger m value in the upper part of the global phase diagram. These results suggest that $CeT_mAl_{2m+2}Si_2$ is a promising platform for the exploration of a novel quantum spin liquid phase in vicinity of the quantum criticality.

In conclusion, we performed electrical resistivity, magnetoresistivity, specific heat, and Hall resistivity measurements on CeRhAl₄Si₂ and constructed a comprehensive T-B phase diagram down to 0.3 K with the field applied along the c-axis. The two successive AFM transitions decrease with increasing field. The first-order AFM transition at $T_{\rm N2}$ is continuously suppressed at 5.5 T while the suppression of the second-order AFM transition at $T_{\rm N1}$ is terminated at a tricritical point 6.6 T and 4.7 K, where it is bifurcated into the first-order AFM transition line and the new

phase transition line. Further experimental work such as neutron scattering on CeRhAl₄Si₂ with field applied along the c-axis will be important to understand the nature of the field-induced multiple quantum phase transitions, especially the intermediate phase that may arise from novel quantum spin liquids.

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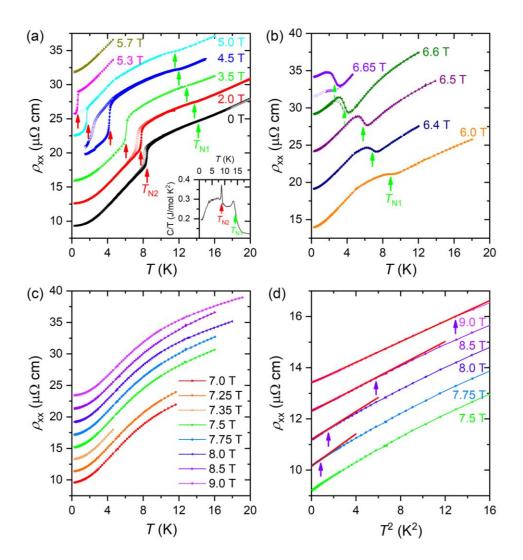


FIG. 1. (a-c) Temperature dependence of in-plane resistivity $\rho_{xx}(T)$ for CeRhAl₄Si₂ at various fields applied along the c-axis. T_{N1} (green arrows) and T_{N2} (red arrows) correspond to the higher second-order and the lower first-order AFM transition temperatures, respectively. After the higher second-order AFM transition changes to a first-order transition above 6.6 T, T_{N1} is marked by the dashed green arrows. Solid symbols represent data measured with increasing temperature and zero-field-cooling. Open symbols represent data measured with decreasing temperature and field-cooling. The first-order nature of transition is revealed by the hysteretic behavior. Inset of (a) shows the temperature dependence of specific heat divided by temperature C/T at 0 T. (d) Low temperature resistivity is plotted as a function of T^2 for fields above 7.5 T. Violet arrows mark the Fermi liquid temperature below which $\rho_{xx}(T)$ follows T^2 dependence. The solid red lines are least-

squares fits to $\rho_{xx}(T) = \rho_0 + AT^2$. For clarity, resistivity data at different fields have been shifted vertically by 3, 5, 2, and 1 $\mu\Omega$ cm in (a–d), respectively.

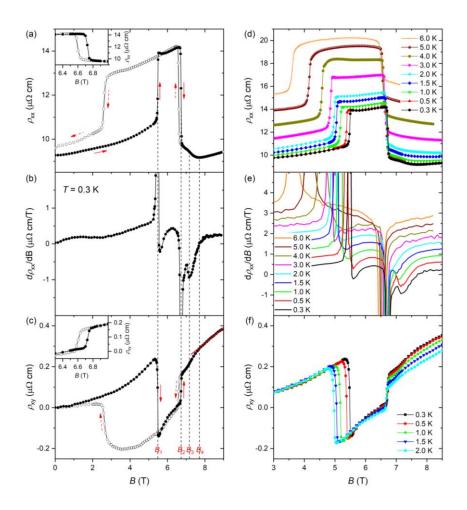


FIG. 2. Isotherms of magnetoresistivity $\rho_{xx}(B)$, differential magnetoresitivity $d\rho_{xx}(B)/dB$, and Hall resistivity $\rho_{xy}(B)$ for CeRhAl₄Si₂ measured at T = 0.3 K (a-c) and at representative temperatures between T = 0.3 and 6.0 K (d-f). A clear hysteresis is visible in the field up and down cycle in (a) and (c), illustrating the first-order nature of the two MMTs at lower temperatures. Solid and dashed arrows indicate field up and down sweeps, respectively. Dashed lines in (a-c) indicate the critical fields marked by B_1 , B_2 , B_3 , and B_4 , corresponding to the sequence of transitions. The insets in (a) and (c) are enlarged views of the hysteresis near the MMT at B_2 . Red line in (c) is the linear fit to $\rho_{xy}(B)$. For clarity, $d\rho_{xx}(B)/dB$ in (e) has been shifted vertically by 0.4 $\mu\Omega$ cm/T.

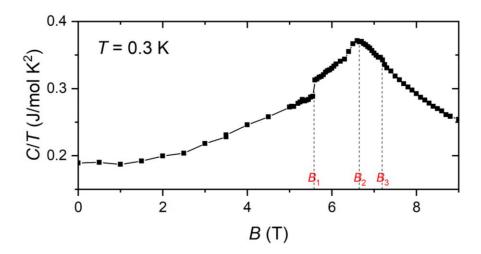


FIG. 3. Field dependence of specific heat divided by temperature C/T for CeRhAl₄Si₂ measured at 0.3 K. Dashed lines indicate the critical fields marked by B_1 , B_2 , and B_3 , corresponding to the critical fields as shown in Fig. 2.

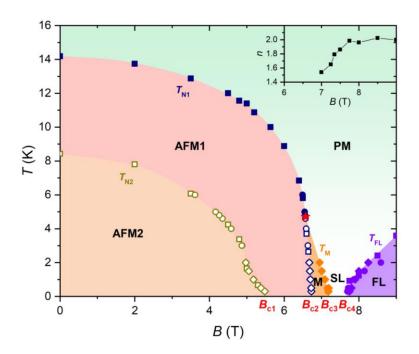


FIG. 4. Temperature-field (T-B) phase diagram of CeRhAl₄Si₂ for field applied along the c-axis. The dark yellow squares, circles, and diamonds denote the lower first-order AFM transition at T_{N2} determined by resistivity $\rho_{xx}(T)$, magnetoresistivity $\rho_{xx}(B)$, and Hall resistivity $\rho_{xy}(B)$ measurements, respectively. The solid navy squares and circles represent the higher second-order

AFM transition at $T_{\rm N1}$ determined by $\rho_{\rm xx}(T)$ and $\rho_{\rm xx}(B)$ measurements, respectively. The open navy squares, circles, and diamonds denote the first-order AFM transition at $T_{\rm N1}$ obtained by $\rho_{\rm xx}(T)$, $\rho_{\rm xx}(B)$, and $\rho_{\rm xy}(B)$ measurements, respectively. The orange circles and diamonds mark the characteristic temperature $T_{\rm M}$ for the new field-induced phase deduced from $\rho_{\rm xx}(B)$ and $\rho_{\rm xy}(B)$ measurements, respectively. The violet circles and diamonds identify the critical fields where the slope of $\rho_{\rm xx}(B)$ recovers to be positive and $\rho_{\rm xy}(B)$ shows linear B-dependence. The violet squares are the onset of the T^2 -dependent resistivity behavior. $B_{\rm c1}$, $B_{\rm c2}$, $B_{\rm c3}$, and $B_{\rm c4}$ correspond to the phase boundaries separating the two antiferromagnetic phases (AFM1 and AFM2), the new field-induced phase (M), the intermediate quantum critical phase (SL), and the Fermi liquid phase (FL). The red star indicates the possible tricritical point. All the first-order phase transition points (open symbols) were taken from either increasing-magnetic field or increasing-temperature measurements with zero-field-cooling mode. Insert shows the field dependence of exponent n resulting from the power law fits to the $\rho_{\rm xx}(T)$ data of the form $\rho_{\rm xx}(T) = \rho_0 + AT^n$. PM represents the paramagnetic phase.